BREAKDOWN AND CAPACITANCE PROPERTIES OF SOME TWO TERMINAL SILICON EPITAXIAL DEVICE STRUCTURES

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CERTIFICATE

This is to certify that the dissertation, 'Breakdown And Capacitance Properties of Some Two Terminal Silicon Epitaxial Device Structures', which is being submitted by Rajendra Kumar for the award of the degree of Doctor of Philosophy to the Indian Institute of Technology, New Delhi, is a record of bonafide research work. He has carried out this research work under my guidance and supervision.

This dissertation has reached the standard fulfilling the requirements of the regulations relating to the degree. The results obtained in this dissertation have not been submitted to any other University or Institute for the award of any degree or diploma.

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